

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Lee et al.

GROUP: Unknown

SERIAL NO: Unknown

EXAMINER: Unknown

FILED: Herewith

**FOR: A METHOD FOR IMPROVING HOLE MOBILITY ENHANCEMENT IN
STRAINED SILICON P-TYPE MOSFET**

**Assistant Commissioner of Patents
Washington, D.C. 20231**

Sir:

INFORMATION DISCLOSURE STATEMENT

In compliance with 37 C.F.R. §§1.56, 1.97, and 1.98, Applicant submits copies of the documents listed on the attached Form PTO-1449.

The Commissioner is authorized to charge Deposit Order Account No. 19-0079 for any further fee that may be required.

Respectfully submitted,

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I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with the United States Postal Service on the date shown below in an envelope, with sufficient postage as first class mail addressed to the Commissioner of Patents and Trademarks, P.O. Box 1450, Alexandria, VA 22313-1450, Attn: Mail Stop Patent Application

Deborah M. Costello
Deborah M. Costello
10/25/03
Date

FORM PTO-1449 (Rev. 5/92) SAMUELS, GAUTHIER & STEVENS LLP 225 Franklin Street, Boston, MA 02110 Telephone: (617) 426-9180	ATTORNEY DOCKET NO. MIT9889 <u>Lee et al.</u> APPLICANT: Herewith FILING DATE:	SERIAL NO. Unknown GROUP: Unknown EXAMINER:Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AJ						
	AK						
	AL						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AM	"Characteristics and Device Design of Sun-100nm Strained Si N- and PMOSFETs"; Rim et al., 2002 Symposium on VLSI Technology Digest of Technical Papers
	AN	"Hole mobility enhancements and alloy scattering-limited mobility in tensile strained Se/SiGe surface channel metal-oxide-semiconductor field-effect transistors: Leitz et al., Journal of Applied Physics, Vol. 92, No. 7; October 1, 2002; pgs: 3745-3751
	AO	

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation consider d, wh th r or n t citation is in c nformanc with MPEP 609; draw line thr ugh citati n if not in conf rmanc and n t consider d. Includ copy of this f rm with next communication t applicant.